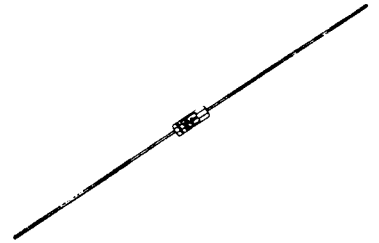


Diac

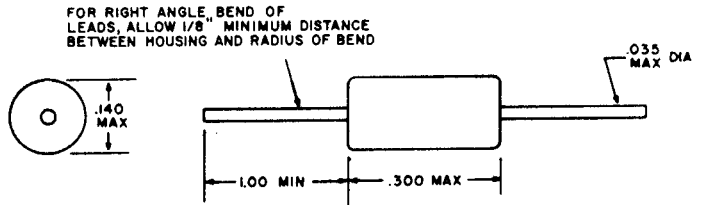
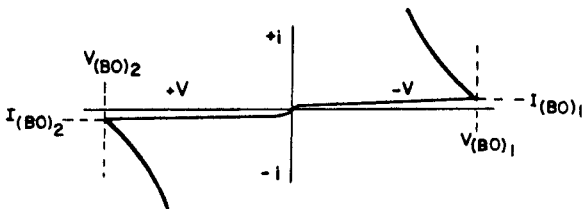
Silicon Bidirectional Trigger

ST2

The DIAC is a diffused silicon bi-directional trigger diode which may be used to trigger the G-E TRIAC or Silicon Controlled Rectifiers. This device has a three-layer structure having negative resistance switching characteristics for both directions of applied voltage.



VOLT – AMPERE CHARACTERISTICS

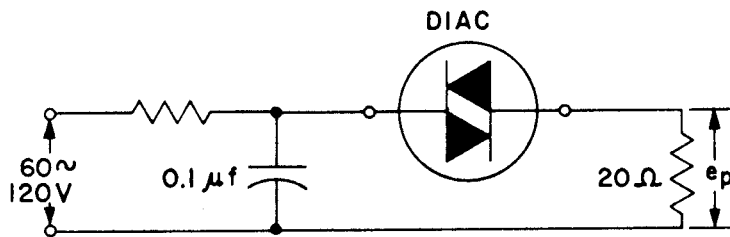


Storage Temperature. T_{STG} -40°C to $+150^{\circ}\text{C}$
 Operating Temperature. T_J -40°C to $+100^{\circ}\text{C}$

MAXIMUM RATINGS at 50°C Ambient

Peak Current (10 μsec duration, 120 cycle repetition rate). $I_p \pm 2$ Amperes Max.
 Peak Output Voltage*. $e_p \pm 3$ Volts Min.

*CIRCUIT FOR PEAK OUTPUT VOLTAGE TEST



CHARACTERISTICS at 25°C Ambient

Test	Symbols	Min.	Typ.	Max.	Units
Breakover Voltage	$V_{(BR)1}$ and $V_{(BR)2}$	28	32	36	Volts
Breakover Voltage Temp. Coefficient		—	0.1	—	%/ $^{\circ}\text{C}$
Breakover Currents	$I_{(BR)1}$ and $I_{(BR)2}$	—	—	200	μamp
Breakover Voltage Symmetry	$ V_{(BR)1} - V_{(BR)2} $	—	—	3.8	Volts